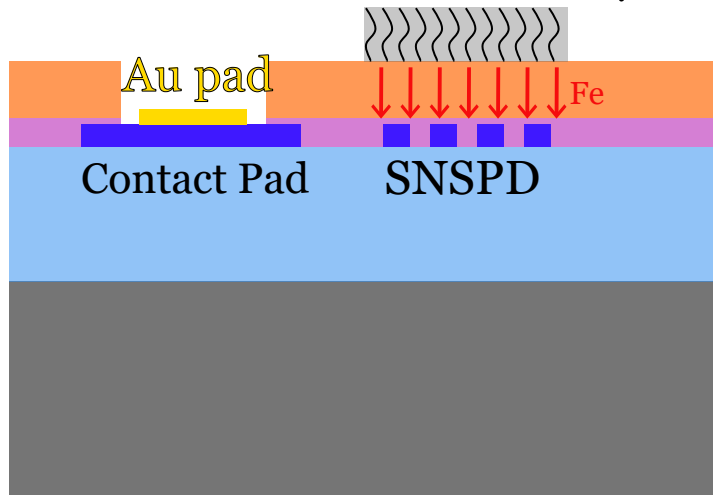


(A)

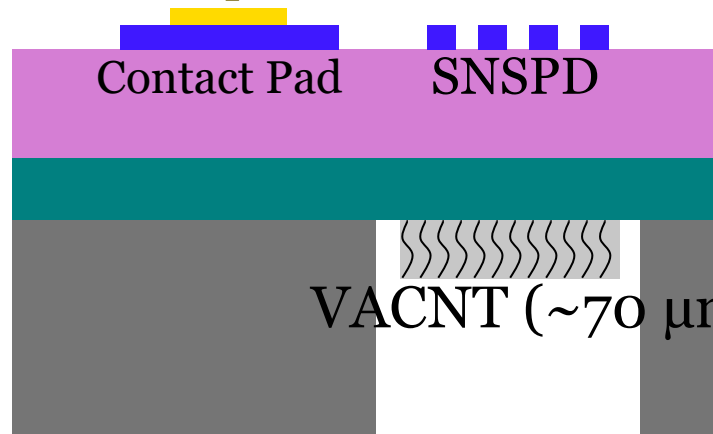
VACNT ($\sim 70\ \mu\text{m}$)



AlN_x (12 nm)
SiN_x (10 nm)
WSi (4 nm)
SiO₂ (150 nm)
Si Wafer (375 μm)

(B)

Au pad



WSi (4 nm)
SiN_x (120 nm)
Al₂O₃ (10 nm)
Si Wafer (375 μm)